## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_A = 25^{\circ}$ C unless otherwise specified.

Symbol	Parameter	Min.	Unit	
T <sub>OPR</sub>	Operating Temperature	-40 to +85		
T <sub>STG</sub>	Storage Temperature	-40 to + 100		
T <sub>SOL-I</sub>	Lead Temperature (Solder Iron) <sup>(1,2,3)</sup>	240 for 5 s		
T <sub>SOL-F</sub>	Lead Temperature (Solder Flow) <sup>(1,2)</sup>	260 for 10 s		
EMMITER				
۱ <sub>F</sub>	Continuous Forward Current	50	mA	
V <sub>R</sub>	Reverse Voltage	5	V	
P <sub>D</sub>	Power Dissipation	100	mW	
SEMSOR				
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V	
V <sub>ECO</sub>	Emitter-Collector Voltage		V	
PD	Power Dissipation <sup>(4)</sup>	100	mW	

Notes:

1. RMA flux is recommended.

2. Methanol or isopropyl alcohols are recommended as cleaning agents.

3. Soldering iron tip 1/16 inch (1.6 mm) minimum from housing.

4. Derate power dissipation linearly 1.33 mW/°C.

## **Electrical / Optical Characteristics**

Values are at  $T_A = 25^{\circ}C$  unless specified otherwise.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
INPUT (Emi	itter)		•		•	
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 20 mA			1.7	V
I <sub>R</sub>	Reverse Leakage Current	V <sub>R</sub> = 5 V			100	μA
$\lambda_{PE}$	Peak Emission Wavelength	I <sub>F</sub> = 20 mA		940		nm
OUTPUT (S	ensor)		•		•	
BV <sub>CEO</sub>	Collector-Emitter Breakdown	$I_{\rm C} = 1  \rm{mA}$	30			V
BV <sub>ECO</sub>	Emitter-Collector Breakdown	I <sub>E</sub> = 0.1 mA	5			V
I <sub>D</sub>	Dark Current	V <sub>CE</sub> = 10 V, I <sub>F</sub> = 0 mA			100	nA
COUPLED					•	•
IC(ON)	QRD1113 Collector Current	$I_F = 20 \text{ mA}, V_{CE} = 5 \text{ V},$ D = 0.050 inch <sup>(5, 7)</sup>	0.300			mA
IC(ON)	QRD1114 Collector Current		1			mA
V <sub>CE(SAT)</sub>	Collector Emitter Saturation Voltage	$I_F = 40 \text{ mA}, I_C = 100 \mu \text{A}, D = 0.050 \text{ inch}^{(5, 7)}$			0.4	V
I <sub>CX</sub>	Cross Talk	$I_F = 20 \text{ mA}, V_{CE} = 5 \text{ V}, E_E = 0^{(6)}$		0.2	10.0	μΑ
t <sub>r</sub>	Rise Time	$V_{CE} = 5 \text{ V}, \text{ R}_{L} = 100 \Omega,$		10		μs
t <sub>f</sub>	Fall time	$I_{C(ON)} = 5 \text{ mA}$		50		μs

Notes:

5. D is the distance from the sensor face to the reflective surface.

6. Crosstalk (I<sub>CK</sub>) is the collector current measured with the indicated current on the input diode and with no reflective surface.

7. Measured using Eastman Kodak natural white test card with 90% diffused reflecting as a reflecting surface.